

Code No: 53009

JAWAHARLAL NEHRU TECHNOLOGICAL UNIVERSITY, HYDERABAD

B.Tech II Year I Semester Examinations, December-2014

ELECTRONIC DEVICES AND CIRCUITS

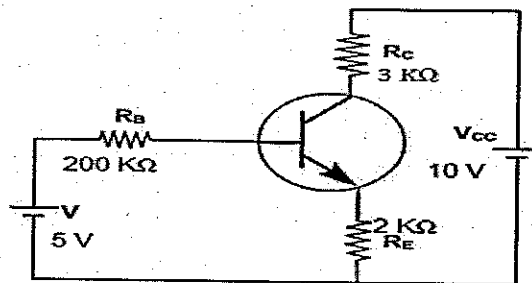
(Common to EEE, ECE, CSE, EIE, BME, IT, MCT, ETM, ICE)

Time: 3 hours

Max. Marks: 75

Answer any five questions
All questions carry equal marks

- 1.a) What are the types of breakdown mechanisms in a diode? Explain the reverse bias characteristics of Zener diode.
 - b) Derive the expression for transition capacitance of a diode.
- 2.a) Design an L-section filter and obtain its expression for ripple factor.
 - b) A fullwave rectifier circuit uses two silicon diodes with a forward resistance of $20\ \Omega$ each. A DC voltmeter connected across the load of $1\text{K}\Omega$ reads 55.4 Volts. Calculate
 - i) I_{rms}
 - ii) Average voltage across each diode
 - iii) Ripple factor
 - iv) Transformer secondary voltage rating.
- 3.a) Obtain a generalized transistor equation for collector current when emitter junction is forward biased and collector junction is reverse biased.
 - b) Find the transistor currents in the circuit as shown in Figure. A silicon transistor with $\beta = 100$ and $I_{\text{co}} = 20\ \text{nA}$ is under consideration.



- 4.a) Draw the circuit diagram of a self bias circuit and explain how to determine the value of R_1 and R_2 .
 - b) An NPN transistor having $\beta = 50$ is used in Common Emitter circuit with $V_{\text{CC}} = 10\ \text{V}$, $R_{\text{C}} = 2\ \text{K}\Omega$. The bias is obtained by connecting $100\ \Omega$ resistor from collector to base. Find the quiescent point and stability factor S.
- 5.a) Draw the BJT hybrid models for CE, CB, CC configurations.
 - b) Compare CE, CB and CC amplifier Configurations.

- 6.a) Obtain the small signal model of JFET. What are the parameters of FET? Give their relationship.
- b) Compare BJT and JFET.
- 7.a) Explain how FET can be used as a voltage variable resistor?
- b) Determine the operating point for the self bias circuit of n-channel JFET given $V_{DD} = 15 \text{ V}$, $R_D = 500 \ \Omega$, $R_S = 1 \text{ K}\Omega$, $R_1 = 12 \text{ K}\Omega$, $R_2 = 4 \text{ K}\Omega$, $I_{DSS} = 8 \text{ mA}$, $V_P = -4\text{V}$.
- 8.a) Explain the principle of operation of Tunnel diode. Also explain the construction, principle of operation of a Photo diode.
- b) Explain the principle and operation of Silicon Controlled Rectifier.

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